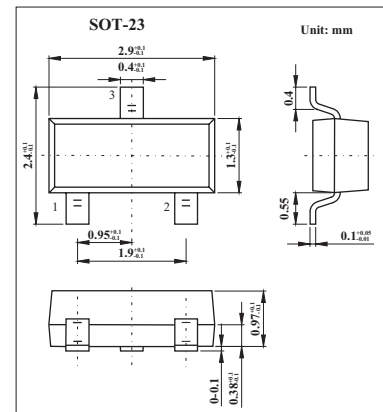


## Silicon Schottky Barrier Diode

## HSM88WA

## ■ Features

- Proof against high voltage.
- MPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse voltage	$V_R$	10	V
Average rectified current	$I_o$	15	mA
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

Note

10ms Sinewave 1pulse

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	$V_F$	$I_F = 1\text{ mA}$	350		420	mV
		$I_F = 10\text{ mA}$	500		580	
Reverse current	$I_R$	$V_R = 2\text{ V}$			0.2	$\mu\text{ A}$
		$V_R = 10\text{ V}$			10	
Capacitance	C	$V_R = 0\text{ V}, f = 1\text{ MHz}$			0.85	pF
Capacitance deviation	$\Delta C$	$V_R = 0\text{ V}, f = 1\text{ MHz}$			0.10	pF
Forward voltage deviation	$\Delta V_F$	$I_F = 10\text{ mA}$			10	mV
ESD-Capability (Note 1)		C=200pF, Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ;  $I_R \geq 400\text{ nA}$  at  $V_R = 2\text{ V}$

## ■ Marking

Marking	C7